

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

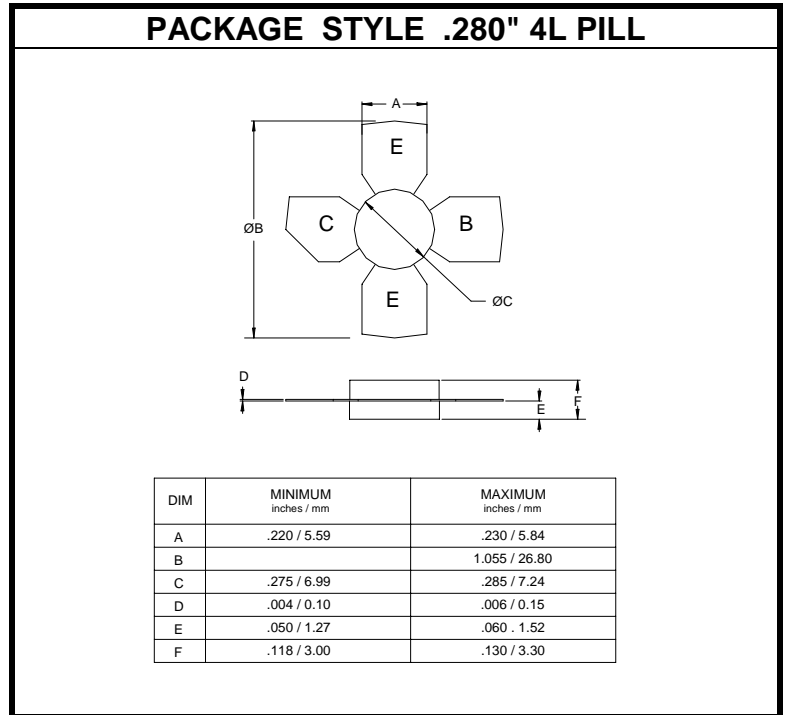
The **MRF616** is Designed for Common Emitter Class C Amplifier Applications in 12.5 Volt UHF Mobile Radios.

FEATURES INCLUDE:

- High Gain, 11 DB Typical
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	250 mA
V_{CB0}	36 V
P_{DISS}	5.0 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	35 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 5.0 mA	36			V
BV_{CEO}	I _C = 50 mA	16			V
BV_{EBO}	I _E = 1.0 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 150 mA	20			---
C_{OB}	V _{CB} = 12.5 V f = 1.0 MHz		3.5		pF
P_G η_C	V _{CE} = 12.5 V P _{OUT} = 1.0 W f = 470 MHz	10	11 65		dB %